



# PSMN047-100NSE

N-channel 100 V 48 mOhm standard level MOSFET in DFN2020 package, designed specifically for high power PoE applications

21 June 2021

Objective data sheet

## 1. General description

New standards and proprietary approaches are enabling Power-over-Ethernet (PoE) systems capable of delivering up to 90 W to each powered device (PD). Such solutions place increased demands on the power sourcing equipment (PSE) in terms of “soft-start”, thermal management and power density requirements. PSMN047-100NSE is designed specifically for high power PoE applications.

## 2. Features and benefits

- Enhanced safe operating area (SOA) for superior linear mode operation
- Low  $R_{DS(on)}$  for low  $I^2R$  conduction losses
- 2 mm x 2 mm space-saving DFN2020 package, 60% smaller than LPAK33
- Very low  $I_{DSS}$  leakage

## 3. Applications

- High power PoE applications (60 W and higher)
- IEEE802.3at and proprietary PoE solutions
- Fault tolerant load switch - Inrush management and eFuse applications
- Battery management applications

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	-	100	V
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}$	-	-	14	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}; \text{Fig. 1}$	-	-	38	W
$T_j$	junction temperature		-55	-	175	°C
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 5\text{ A}; T_j = 25\text{ °C}$	-	36	48	mΩ
		$V_{GS} = 10\text{ V}; I_D = 5\text{ A}; T_j = 100\text{ °C}$	-	60	77	mΩ
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$I_D = 25\text{ A}; V_{DS} = 50\text{ V}; V_{GS} = 10\text{ V}; T_j = 25\text{ °C}$	[tbd]	1.4	[tbd]	nC
$Q_{G(tot)}$	total gate charge		[tbd]	7.2	[tbd]	nC
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 11\text{ A}; V_{sup} \leq 100\text{ V}; R_{GS} = 50\text{ Ω}; V_{GS} = 10\text{ V}; T_{j(init)} = 25\text{ °C}; \text{unclamped}$	[1]	-	14	mJ

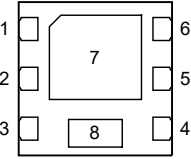
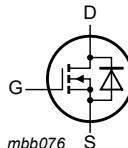
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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Source-drain diode</b>						
$Q_r$	recovered charge	$I_S = 25 \text{ A}$ ; $di_S/dt = -100 \text{ A}/\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ; $V_{DS} = 50 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 3</a>	-	21.9	-	nC

[1] Protected by 100% test

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	 <p>Transparent top view <b>DFN2020M-6 (SOT1220-2)</b></p>	 <p>mbb076</p>
2	D	drain		
3	G	gate		
4	S	source		
5	D	drain		
6	D	drain		
7	D	drain		
8	S	source		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN047-100NSE	DFN2020M-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body 2 x 2 x 0.65 mm	SOT1220-2

## 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$25 \text{ }^\circ\text{C} \leq T_j \leq 175 \text{ }^\circ\text{C}$	-	100	V
$V_{DGR}$	drain-gate voltage	$25 \text{ }^\circ\text{C} \leq T_j \leq 175 \text{ }^\circ\text{C}$ ; $R_{GS} = 20 \text{ k}\Omega$	-	100	V
$V_{GS}$	gate-source voltage		-20	20	V
$P_{tot}$	total power dissipation	$T_{mb} = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 1</a>	-	38	W
$I_D$	drain current	$V_{GS} = 10 \text{ V}$ ; $T_{mb} = 25 \text{ }^\circ\text{C}$	-	14	A
		$V_{GS} = 10 \text{ V}$ ; $T_{mb} = 100 \text{ }^\circ\text{C}$	-	10	A
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10 \text{ }\mu\text{s}$ ; $T_{mb} = 25 \text{ }^\circ\text{C}$	-	56	A
$T_{stg}$	storage temperature		-55	175	$^\circ\text{C}$
$T_j$	junction temperature		-55	175	$^\circ\text{C}$
$T_{slid(M)}$	peak soldering temperature		-	260	$^\circ\text{C}$
<b>Source-drain diode</b>					
$I_S$	source current	$T_{mb} = 25 \text{ }^\circ\text{C}$	-	14	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10 \text{ }\mu\text{s}$ ; $T_{mb} = 25 \text{ }^\circ\text{C}$	-	56	A

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Symbol	Parameter	Conditions		Min	Max	Unit
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 11\text{ A}$ ; $V_{sup} \leq 100\text{ V}$ ; $R_{GS} = 50\ \Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; unclamped	[1]	-	14	mJ
$I_{AS}$	non-repetitive avalanche current	$V_{sup} = 100\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; $R_{GS} = 50\ \Omega$	[1]	-	11	A

[1] Protected by 100% test

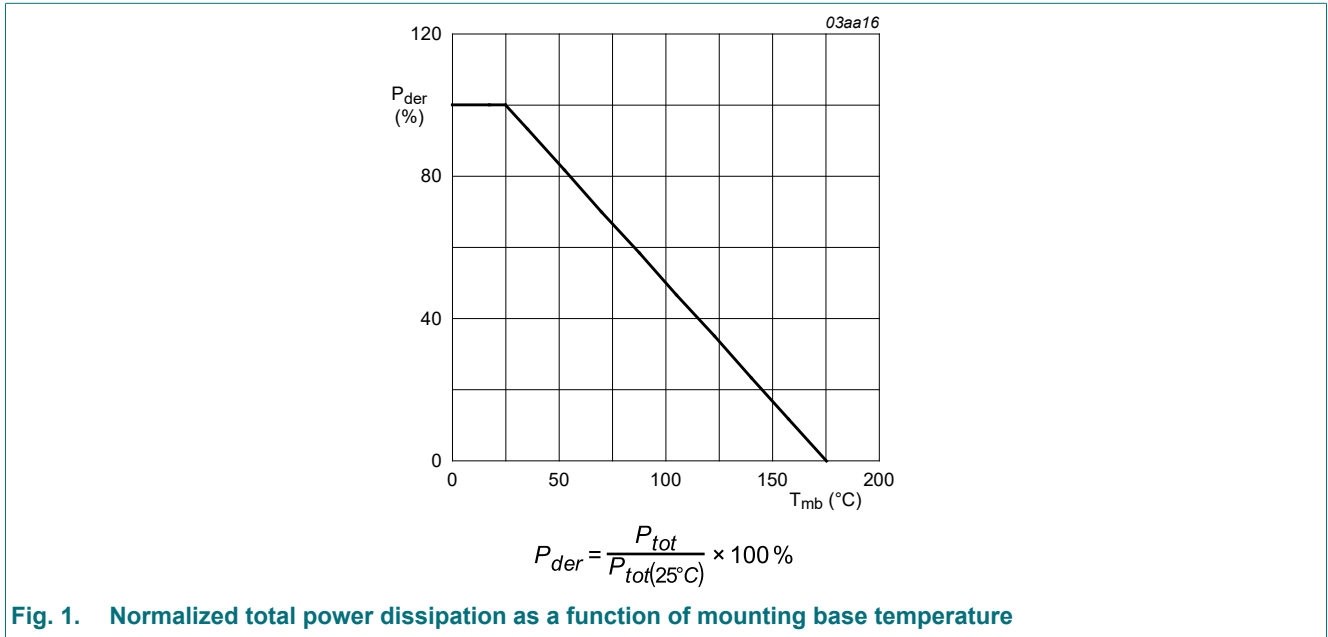


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

## 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base			-	[tbd]	4	K/W

## 9. Characteristics

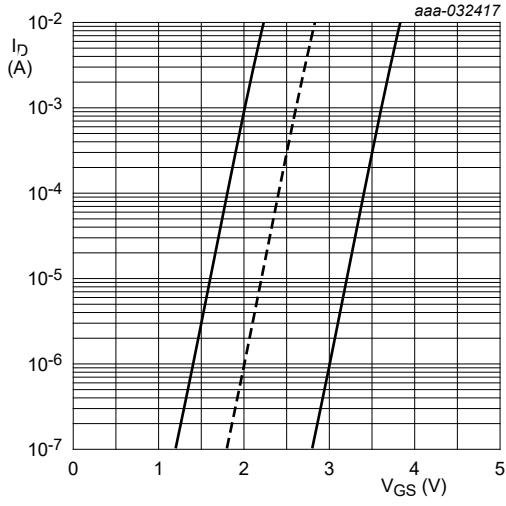
Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
<b>Static characteristics</b>							
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\ \mu\text{A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$		100	-	-	V
		$I_D = 250\ \mu\text{A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = -55\text{ }^\circ\text{C}$		90	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\text{ mA}$ ; $V_{DS}=V_{GS}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; Fig. 2		2	2.6	3.6	V
		$I_D = 1\text{ mA}$ ; $V_{DS}=V_{GS}$ ; $T_j = 175\text{ }^\circ\text{C}$		-	[tbd]	-	V
		$I_D = 1\text{ mA}$ ; $V_{DS}=V_{GS}$ ; $T_j = -55\text{ }^\circ\text{C}$		-	[tbd]	-	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	$25\text{ }^\circ\text{C} \leq T_j \leq 150\text{ }^\circ\text{C}$		-	[tbd]	-	mV/K

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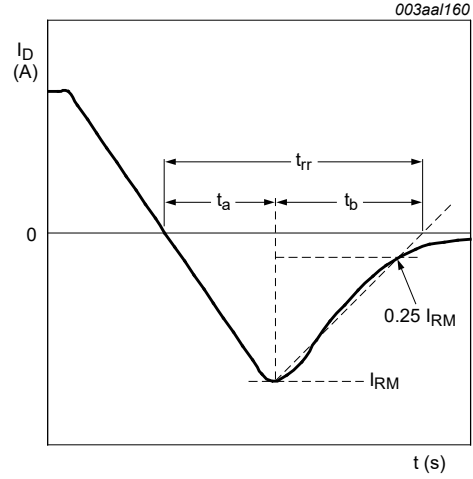
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	[tbd]	1	μA
		V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>DS</sub> = -20 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DS(on)</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C	-	36	48	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 100 °C	-	60	77	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 175 °C	-	84	112	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	[tbd]	1	[tbd]	Ω
<b>Dynamic characteristics</b>						
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C	[tbd]	7.2	[tbd]	nC
		I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V	-	3.8	-	nC
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C	[tbd]	2.1	[tbd]	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge		-	1.4	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	0.7	-	nC
Q <sub>GD</sub>	gate-drain charge		[tbd]	1.4	[tbd]	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; T <sub>j</sub> = 25 °C	-	4.5	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C	[tbd]	507	[tbd]	pF
C <sub>oss</sub>	output capacitance		[tbd]	111	[tbd]	pF
C <sub>rss</sub>	reverse transfer capacitance		[tbd]	3.5	[tbd]	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 50 V; R <sub>L</sub> = 2 Ω; V <sub>GS</sub> = 10 V; R <sub>G(ext)</sub> = 5 Ω; T <sub>j</sub> = 25 °C	-	1.8	-	ns
t <sub>r</sub>	rise time		-	1.5	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	4.4	-	ns
t <sub>f</sub>	fall time		-	2.2	-	ns
<b>Source-drain diode</b>						
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 25 A; di <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; <a href="#">Fig. 3</a>	-	30.3	-	ns
Q <sub>r</sub>	recovered charge	I <sub>S</sub> = 25 A; di <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 3</a>	-	21.9	-	nC

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$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 5\text{ V}$

**Fig. 2. Sub-threshold drain current as a function of gate-source voltage**

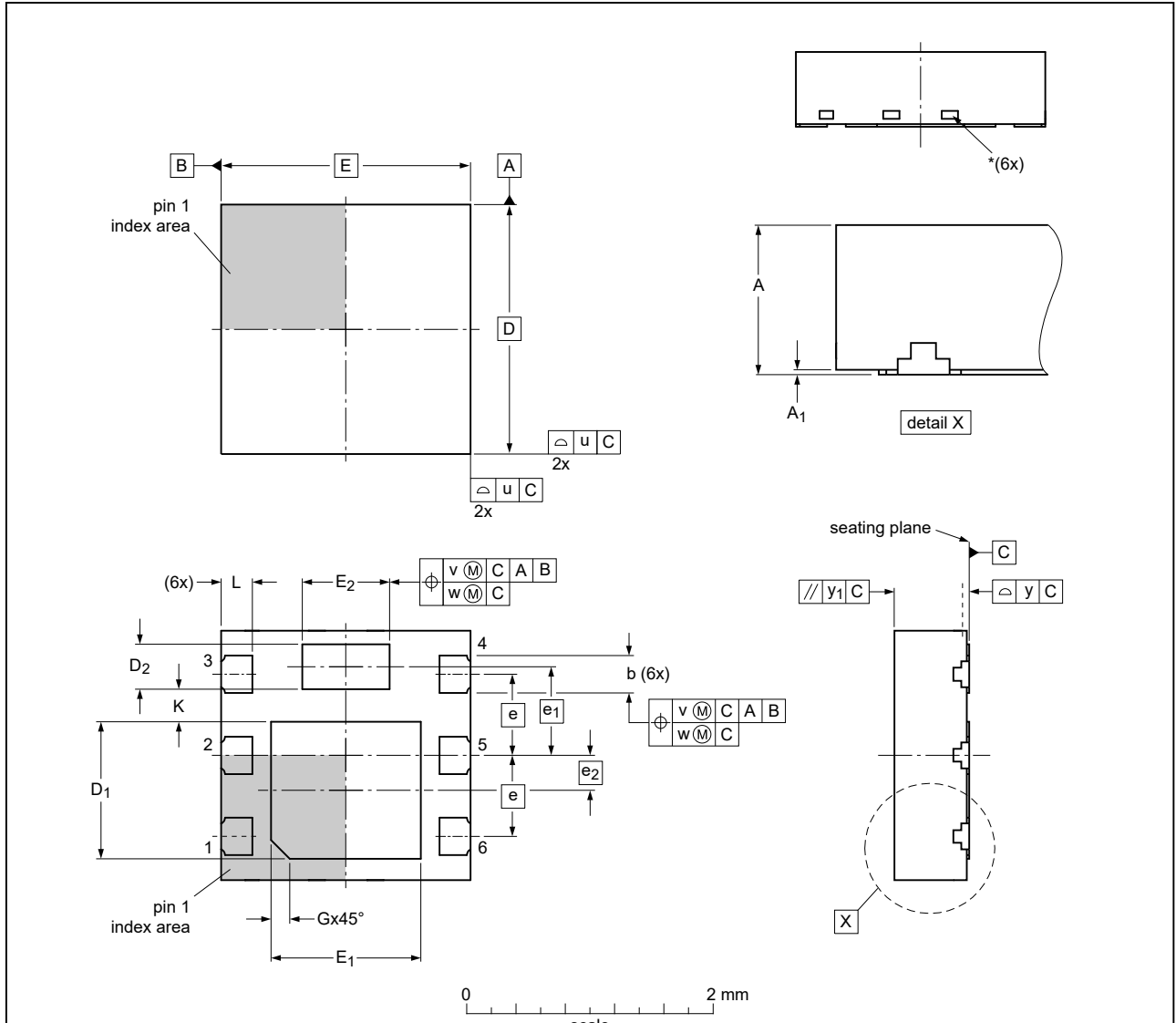


**Fig. 3. Reverse recovery timing definition**

### 10. Package outline

DFN2020M-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body 2 x 2 x 0.65 mm

SOT1220-2



Dimensions (mm are the original dimensions)

Unit	A	A <sub>1</sub>	b	D	D <sub>1</sub>	D <sub>2</sub>	E	E <sub>1</sub>	E <sub>2</sub>	e	e <sub>1</sub>	e <sub>2</sub>	G	K	L	u	v	w	y	y <sub>1</sub>
min	0.55	0	0.25	1.0	0.31	1.1	0.6													
mm nom	0.60	0.02	0.30	2	1.1	0.36	2	1.2	0.7	0.65	0.71	0.28	0.15 (ref)	0.2	0.20	0.25	0.05	0.1	0.05	0.05
max	0.65	0.04	0.35	1.2	0.41	1.3	0.8									0.30				

Note

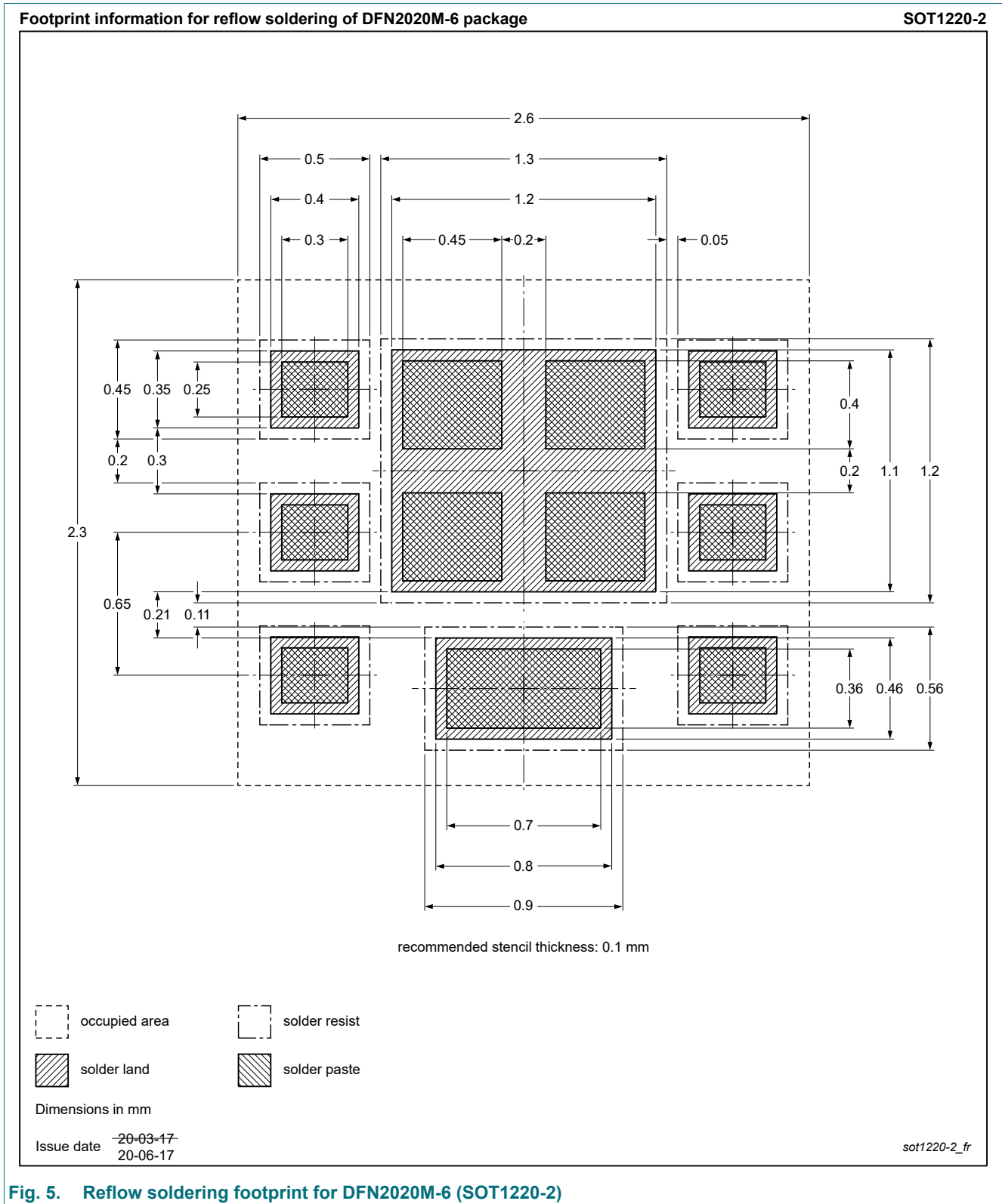
1. Dimension A is including plating thickness.
2. \* Visible depend upon used manufacturing technology.

sot1220-2\_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1220-2		---				-20-03-31- 20-04-01

Fig. 4. Package outline DFN2020M-6 (SOT1220-2)

### 11. Soldering



**Fig. 5. Reflow soldering footprint for DFN2020M-6 (SOT1220-2)**

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## 12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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